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Memorandum

DATE: November 23, 1992
TO: B. Fafaul/311
FROM: K. Sahu *KS*
SUBJECT: Radiation Report on FAST/MUE
Part No. 5962-9098501MRA (54AC521)
Control No. 6115

PPM-92-282

cc: R. Kolecki/740.4
T. Miccolis
A. Sharma/311 *AS*
Library/300.1 ✓
L. Cusick/740.4

A radiation evaluation was performed on 54AC521 (8-Bit Identity Comparator) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 5, 10, 20, 40 and 60 krads*. After 60 krads, parts were annealed at +25°C for 168 hours. The irradiation was then continued to 100 krads (cumulative). The dose rate was between 0.24 and 2.0 krads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits** listed in Table III. These tests included three functional tests at 1.0MHz with VCC = 3.0V, 4.5V, and 5.5V.

All ten parts passed initial (pre-rad) electrical tests. All irradiated parts passed all electrical tests up to and including the 20-krad irradiation step. After the 40-krad irradiation, three parts (SN 54, 56 and 57) exceeded the maximum specification limit of 2 uA for ICCH with readings ranging from 2.22 to 3.16 uA. All other irradiated parts continued to pass at this irradiation step. After the 60-krad irradiation, four parts (SN 54, 56, 57 and 58) exceeded the maximum specification limit for ICCH, with readings ranging from 2.12 to 4.35 uA. After annealing for 168

*The term rads, as used in this document, means rads(silicon).
**These are manufacturers' non-irradiated data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

hours at 25°C, all irradiated parts recovered to within the specification limits for ICCH. After continued irradiation to 100 krads (cumulative), seven parts (SN 53, 54, 55, 56, 57, 58 and 59) exceeded the maximum specification limits for ICCH, with readings ranging from 2.17 to 6.04 uA and four parts (SN 53, 54, 56 and 57) exceeded the maximum specification limit of 2 uA for ICCL, with readings ranging from 2.06 to 2.30 uA.

After a final annealing at 100°C, no rebound effects were observed.

All parts passed all functional tests throughout all irradiation and annealing steps.

Table IV provides a summary of the functional test results, as well as the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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TABLE I. Part Information

Generic Part Number:	54AC521
Part Number:	5962-9098501MRA
FAST/MUE Control Number:	6115
Charge Number:	C23988
Manufacturer:	National Semiconductor Corp.
Lot Date Code:	9236A
Quantity Tested:	10
Serial Numbers of Radiation Samples:	53, 54, 55, 56, 57, 58, 59, 60
Serial Numbers of Control Samples:	51, 52
Part Function:	8-Bit Identity Comparator
Part Technology:	CMOS
Package Style:	20-pin DIP
Test Engineer:	J. Lander

TABLE II. Radiation Schedule for 54AC521

EVENTS	DATE
1) Initial Electrical Measurements	10/20/92
2) 5 KRAD IRRADIATION (0.25 krads/hour)	10/20/92
POST-5 KRAD ELECTRICAL MEASUREMENT	10/21/92
3) 10 KRAD IRRADIATION (0.25 krads/hour)	10/21/92
POST-10 KRAD ELECTRICAL MEASUREMENT	10/22/92
4) 20 KRAD IRRADIATION (0.50 krads/hour)	10/22/92
POST-20 KRAD ELECTRICAL MEASUREMENT	10/23/92
5) 40 KRAD IRRADIATION (0.31 KRADS/HOUR)	10/23/92
POST-40 KRAD ELECTRICAL MEASUREMENT	10/27/92
6) 60 KRAD IRRADIATION (1.11 KRADS/HOUR)	10/27/92
POST-60 KRAD ELECTRICAL MEASUREMENT	10/28/92
7) 168 HOUR ANNEALING @25°C	10/28/92
POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENT	11/04/92
8) 100 KRAD IRRADIATION (2.23 KRADS/HOUR)	11/04/92
POST-100 KRAD ELECTRICAL MEASUREMENT	11/05/92
9) 168 HOUR ANNEALING @100°C*	11/05/92
POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENT	11/13/92

ALL ELECTRICAL MEASUREMENTS WERE PERFORMED AT 25°C.

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS; SEE FIGURE 1.

*High temperature annealing is performed to accelerate long term time dependent effects (TDE), namely, the "rebound" effect due to the growth of interface states after the radiation exposure. For more information on the need to perform this test, refer to MIL-STD-883D, Method 1019, Para. 3.10.1.

Table III. Electrical Characteristics of 54AC521

PART NO. : 5962-90985J1MRA GENERIC : 54AC521DMQ3		PART DESCRIPTION : 8-BIT 10-ENTRY COMPARATOR.		PCN : S170584A		
LOCATION			TEST SPECIFICATIONS			
DISK LABEL : LIB 25 DIRECTORY : DATA\PRDGRAMS.584J		DESC # 5962-90985 MFG : NATIONAL SEMICONDUCTOR		DATE : 02/13/92		
FUNCTIONAL TESTS						
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C ONLY
FUNCT 1	5.00V	0.00V	5.00V	FREQ=1.00MHZ	I/O	VOL<1.5V / VOH>1.5V
FUNCT 2	4.50V	0.00V	4.50V	FREQ=1.00MHZ	I/O	VOL<1.5V / VOH>1.5V
FUNCT 3	5.50V	0.00V	5.50V	FREQ=1.00MHZ	I/O	VOL<1.5V / VOH>1.5V
DC PARAMETRIC TESTS						
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C ONLY
VOH1	5.00V	0.90V	2.10V	LOAD=-50uA	OUTS	>+2.90V / <+3.00V
VOH2	4.50V	1.35V	3.15V	LOAD=-50uA	OUTS	>+4.40V / <+4.50V
VOH3	5.50V	1.65V	3.85V	LOAD=-50uA	OUTS	>+5.40V / <+5.50V
VOH4	5.00V	0.90V	2.10V	LOAD=-4mA	OUTS	>+2.40V / <+3.00V
VOM5	4.50V	1.35V	3.15V	LOAD=-24mA	OUTS	>+3.70V / <+4.50V
VFIx	5.50V	1.65V	3.85V	LOAD=-2mA	PV+T	>+3.70V / <+4.50V
VOH7	5.50V	1.65V	3.85V	LOAD=-50mA	OUTS	>+3.85V / <+5.50V
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C ONLY
VOL1	5.00V	0.90V	2.10V	LOAD=+50uA	OUTS	>+0.00V / <+0.10V
VOL2	4.50V	1.35V	3.15V	LOAD=+50uA	OUTS	>+0.00V / <+0.10V
VOL3	5.50V	1.65V	3.85V	LOAD=+50uA	OUTS	>+0.00V / <+0.10V
VOL4	5.00V	0.90V	2.10V	LOAD=+12mA	OUTS	>+0.00V / <+0.40V
VOL5	4.50V	1.35V	3.15V	LOAD=+24mA	OUTS	>+0.00V / <+0.40V
VOL6	5.50V	1.65V	3.85V	LOAD=+24mA	OUTS	>+0.00V / <+0.40V
VOL7	5.50V	1.65V	3.85V	LOAD=+50mA	OUTS	>+0.00V / <+1.65V
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C ONLY
VIC	OPEN	N/A	N/A	IIN = -3mA	INS	>+1.5V / <-0.4V
IIN	5.50V	0.00V	5.50V	VIN = 5.5V	INS	>+0.00uA / <+0.10uA
IIL	5.50V	0.00V	5.50V	VIN = 0.0V	INS	>+0.10uA / <+0.00uA
ICCH	5.50V	0.00V	5.50V	VIN = 5.5V	VCC	>+0.00uA / <+2.00uA
ICCL	5.50V	0.00V	5.50V	VIN = 0.0V	VCC	>+0.00uA / <+2.00uA
AC PARAMETRIC TESTS						
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C
IPLH1_A	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 12.5ns
IPLH1_B	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 12.5ns
IPLH1_C	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 12.5ns
IPLH1_D	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 12.5ns
IPLH1_E	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 9.0ns
IPLH1_F	5.0V	0.0V	5.0V	F=1MHZ/VCMP=1.50V	OUTPUTS	> 1.0ns / < 9.0ns
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C
IPLH2_A	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 9.0ns
IPLH2_B	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 9.0ns
IPLH2_C	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 9.0ns
IPLH2_D	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 9.0ns
IPLH2_E	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 6.5ns
IPLH2_F	4.5V	0.0V	4.5V	F=1MHz/VCMP=2.25V	OUTPUTS	> 1.0ns / < 6.5ns
COMMENTS / EXCEPTIONS						
(1) VIL & VIH were tested during VOL & VOH tests as Go/NoGo.						
(2) VIL Positive is not performed because S-50 cannot hook up VCC to GND and open GND dynamically.						
HARDWARE REQUIREMENTS			TEMPERATURE TESTING CAPABILITY			
DEVICE CONFIGURATION : 20-PIN DIP LOAD BOARD # 2 OR 17 : JUMP/SWITCH GND TO PIN # 10			+25 DEG. C. [x] Only			
ATE PROGRAMMER : JUAN R. LANDER			DATE : 20 OCT 92			

TABLE IV: Summary of Electrical Measurements After Total Dose Exposures and Annealing for 54AC521 1/

Parameters	Spec. Lim./2 min max		Total Dose Exposure (TDE) (krads)												Anneal		TDE		Anneal	
			Initial		5		10		20		40		60		168 hrs @25°C		100 krads		168 hrs @100°C	
			mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd
FUNC1, 1 MHz, 3.0 V	PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS	
FUNC2, 1 MHz, 4.5 V	PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS	
FUNC3, 1 MHz, 5.5 V	PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS	
VOH1 V	2.9	3.0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0
VOH3 V	5.4	5.5	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	.01	5.49	0	5.49	0
VOH5 V	3.7	4.5	4.20	0	4.20	0	4.20	0	4.20	0	4.20	0	4.20	0	4.19	.01	4.19	0	4.19	.01
VOH7 V	3.85	5.5	4.95	.01	4.94	0	4.94	0	4.94	0	4.94	.01	4.94	.01	4.91	.03	4.93	.01	4.91	.02
VOL1/3 mV	0	100	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
VOL7 mV	0	1650	379	3.9	378	3.7	379	3.8	377	2.9	379	4.5	378	3.8	392	12	392	2.8	395	8.2
VIC- mV	-1500	-400	-730	1.5	-731	1.7	-731	1.8	-731	1.8	-733	1.7	-738	1.8	-736	2.0	-737	1.6	-729	2.1
IIH nA	0	100	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
IIL nA	-100	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
ICCH uA	0	2.0	0.02	.04	0.02	.05	0.23	0.1	0.99	0.4	1.66	.77	2.28	1.1	0.55	.26	3.30	1.4	0.09	.04
ICCL uA	0	2.0	0.01	.02	0.01	.02	0.08	.02	0.37	0.1	0.70	.22	1.03	.31	0.33	.08	1.81	0.4	0.01	.01
TPH1_A ns	1.0	12.5	8.46	0.1	8.44	.05	8.50	.06	8.81	.06	8.84	.04	8.81	0.1	8.02	.06	8.07	.06	8.60	.07
TPH1_A ns	1.0	12.5	9.48	.07	9.52	.08	9.52	.08	9.58	.08	9.55	.09	9.57	0.1	10.1	.08	10.2	.08	10.5	.08
TPH1_B ns	1.0	12.5	8.26	0.1	8.28	.04	8.30	.05	8.23	.04	8.27	.05	8.18	.02	7.85	.08	7.92	.05	8.38	.06
TPH1_B ns	1.0	12.5	9.24	.07	9.29	.07	9.28	.07	9.65	.11	9.74	.10	9.67	0.1	9.79	.08	9.90	.08	10.2	.08
TPH1_I ns	1.0	9.0	6.37	.04	6.32	.05	6.33	.06	6.75	.05	6.71	.05	6.65	.04	6.45	.02	6.41	.04	7.03	.07
TPH1_I ns	1.0	9.0	6.67	.07	6.67	.08	6.67	.07	6.71	.06	6.69	.08	6.67	.05	6.47	.07	6.59	0.1	6.60	.06
TPH2_A ns	1.0	9.0	7.24	.03	7.24	.03	7.27	.03	7.62	.03	7.65	.01	7.62	.04	6.76	.02	6.82	.04	7.02	.05
TPH2_A ns	1.0	9.0	7.81	.05	7.82	.05	7.82	.05	7.73	.03	7.78	.05	7.71	.04	8.28	.06	8.33	.05	8.46	.04
TPH2_B ns	1.0	9.0	7.10	.04	7.14	.03	7.16	.03	7.11	.05	7.15	.05	7.04	.02	6.64	.05	6.71	.03	6.84	.04
TPH2_B ns	1.0	9.0	7.65	.04	7.69	.05	7.67	.04	8.05	.06	8.10	.06	8.00	.06	8.09	.03	8.11	.03	8.27	.05
TPH2_I ns	1.0	6.5	5.84	.03	5.77	.03	5.77	.03	6.24	.07	6.04	.02	5.98	.06	5.86	.03	5.79	.03	6.17	.03
TPH2_I ns	1.0	6.5	5.89	.04	5.88	.05	5.87	.05	5.84	.04	5.82	.05	5.77	.03	5.64	.06	5.75	.04	5.67	.05

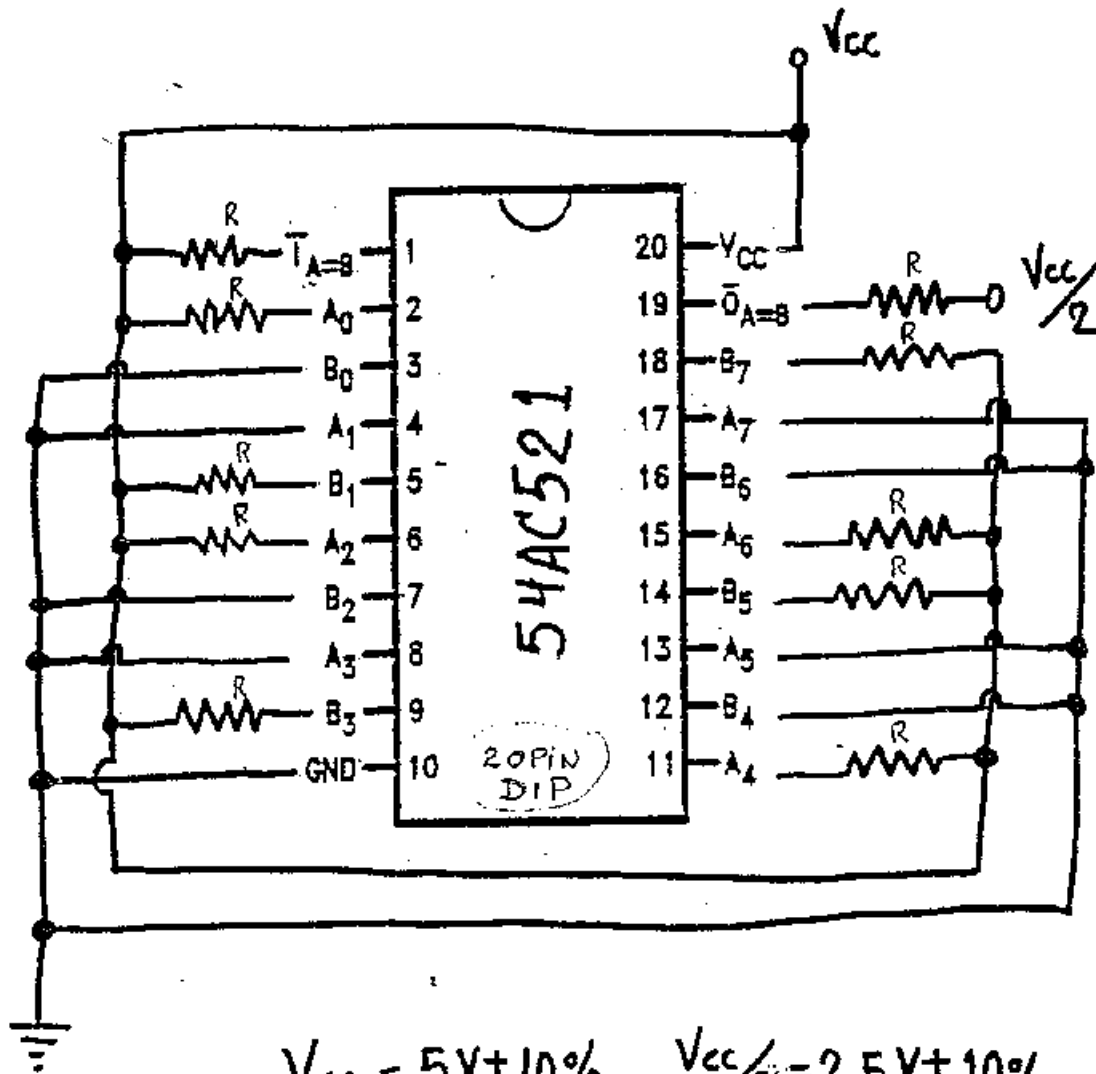
Notes:

1/ The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.

2/These are manufacturers' non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.

3/No significant variation was observed in VOL1 - VOL7 during irradiation and annealing. Additional data on VOL2 - VOL6 are available on request.

Figure 1. Radiation Bias Circuit for 54AC161



$$V_{CC} = 5V \pm 10\% , V_{CC}/2 = 2.5V \pm 10\%$$

$$R = 1K\Omega \pm 5\% , 1/4 W$$

$$T_A = +25^{\circ}C$$